

IS471F

OPIC Light Detector with Built-in Signal Processing Circuit for Light Modulation System

■ Features

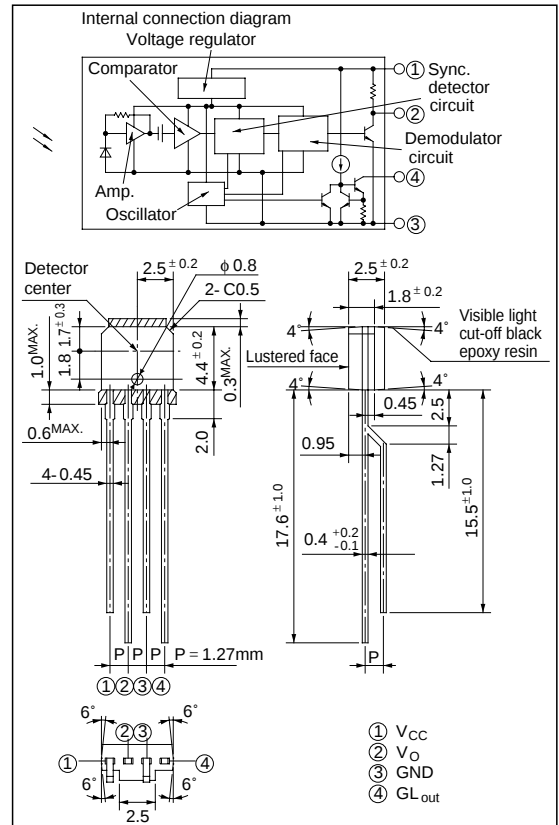
1. Impervious to external disturbing lights due to light modulation system
2. Built-in pulse driver circuit and sync. detector circuit on the emitter side
3. A wide range of operating supply voltage (V_{CC} : 4.5 to 16V)

■ Applications

1. Optoelectronic switches
2. Copiers, printers
3. Facsimiles

■ Outline Dimensions

(Unit : mm)



*"OPIC" (Optical IC) is a trademark of the SHARP Corporation.
An OPIC consists of a light-detecting element and signal-processing circuit integrated onto a single chip.

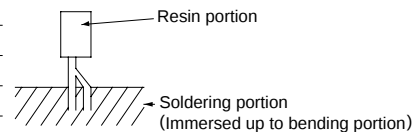
■ Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Rating	Unit
Supply voltage		V_{CC}	-0.5 to 16	V
Output	Output voltage	V_O	16	V
	Output current	I_O	50	mA
*1 GL output	Output voltage	V_{GL}	16	V
Power dissipation		P	250	mW
Operating temperature		T_{opr}	-25 to +60	$^\circ\text{C}$
Storage temperature		T_{stg}	-40 to +100	$^\circ\text{C}$
*2 Soldering temperature		T_{sol}	260	$^\circ\text{C}$

*1 Applies to GL_{out} terminal

*2 For 5 seconds at the position shown in the right figure



■ Electro-optical Characteristics

(V_{CC}= 5V, Ta= 25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating supply voltage		V _{CC}	-	4.5	-	16	V
Supply current		I _{CC}	V _O , GL _{out} terminals shall be opened.	-	3.5	7.0	mA
Output	Low level output voltage	V _{OL}	I _{OL} = 16mA, E _{VP} = 500lx, E _{VD} = 0 ^{*3}	-	0.15	0.35	V
	High level output voltage	V _{OH}	E _{VD} = E _{VP} = 0 ^{*3}	4.97	-	-	V
	Output short circuit current	I _{OS}	E _{VP} = E _{VD} = 0 ^{*3}	0.25	0.5	1.0	mA
GL output	Low level output current	I _{GL}	V _{GL} = 1.2V	40	55	70	mA
	^{*4} Pulse cycle	t _p	-	70	130	220	μs
	^{*4} Pulse width	t _w	-	4.4	8	13.7	μs
^{*5} “Low→High” threshold irradiance		E _{ePLH}	E _{eD} = 0 ^{*3} Light emitting diode (λ _p = 940nm) ^{*6}	-	0.4	2.66	μW/mm ²
^{*5} “High→Low” threshold irradiance		E _{ePHL}		-	0.7	2.8	μW/mm ²
Hysteresis		E _{ePLH} /E _{ePHL}		0.45	0.65	0.95	-
Response time	“High→Low” propagation delay time	t _{PHL}	^{*6}	-	400	670	μs
	“Low→High” propagation delay time	t _{PLH}	^{*6}	-	400	670	μs
^{*7} External disturbing light illuminance		E _{VDX}	E _{ep} = 7.5 μW/mm ² , ^{*3} λ _p = 940nm	2000	7500	-	lx

^{*3} E_{eP} represents illuminance of signal light in sync with the low level timing of output at GL_{out} terminal.

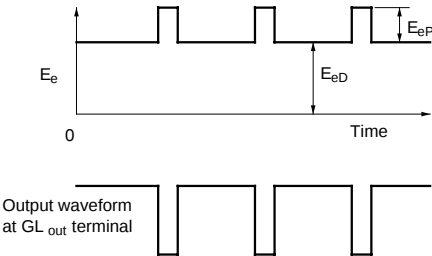
E_{eD} represents illuminance of DC light. For detail, see Fig. 1.

Light source: Infrared light emitting diode (λ_p= 940nm)

E_{VP} represents illuminance of signal light in sync with the low level timing of output at GL_{out} terminal.

E_{VD} represents illuminance of DC light. Note that the light source is CIE standard light source A.

Fig.1



(Note) Fig. 1 shows the output waveform at GL_{out} terminal with **IS471F** connected as shown in Fig. 3.

^{*4} Pulse cycle (t_p), pulse width (t_w) are defined as shown in Fig. 2.

The waveform shown in Fig. 2 is the output voltage waveform at GL_{out} terminal with **IS471F** connected as shown in Fig. 3

Fig.2

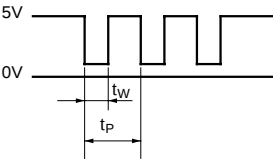
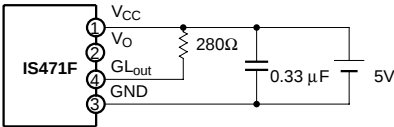


Fig.3



^{*5} Defined as E_{ep} that causes the output to go “ Low to High” (or“ High to Low”).

*6 Test circuit for response time, threshold irradiance is shown in Fig. 4.

Fig. 4

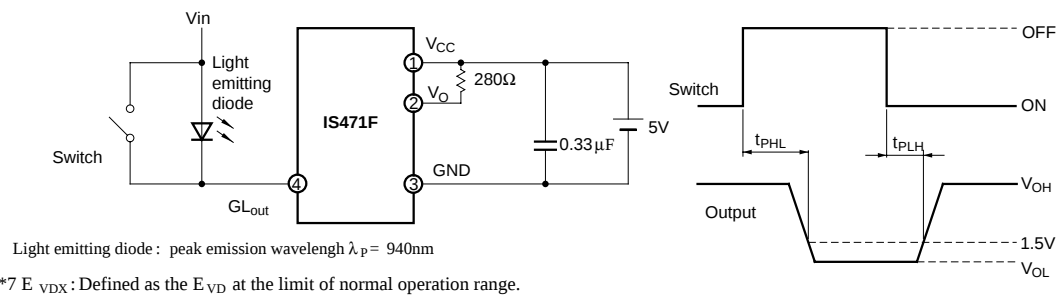


Fig. 5 Power Dissipation vs. Ambient Temperature

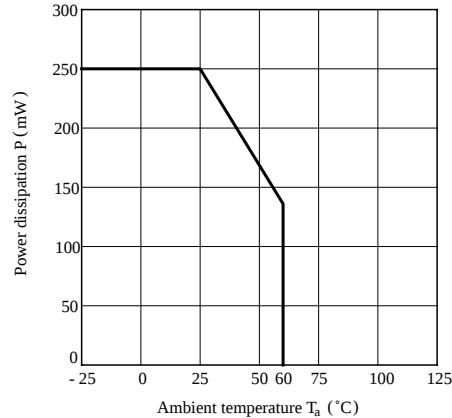


Fig. 6 Low Level Output Voltage vs. Low Level Output Current

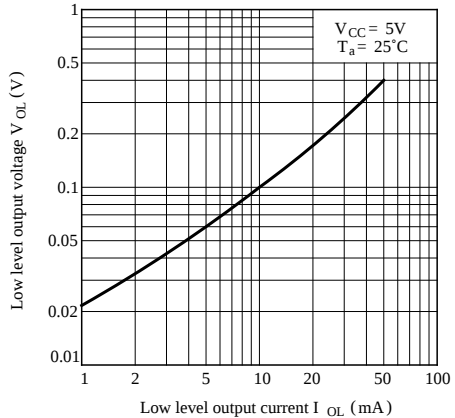


Fig. 7 Low Level Output Voltage vs. Ambient Temperature

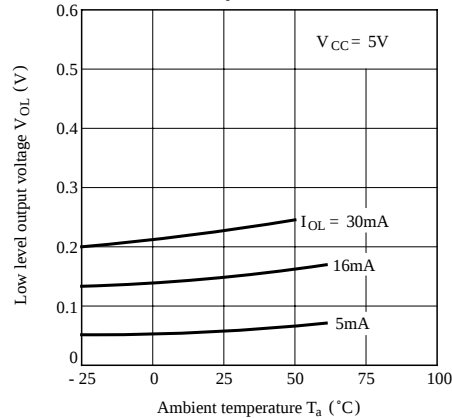


Fig. 8 Supply Current vs. Supply Voltage

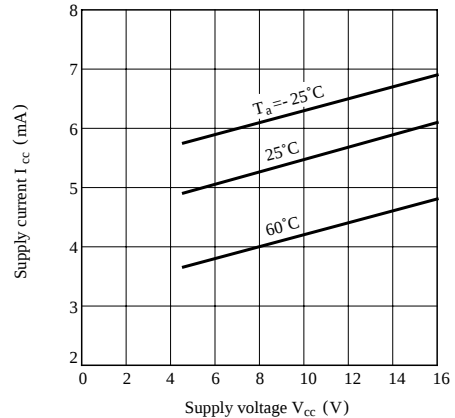


Fig. 9 Low Level Output Current vs. Supply Voltage

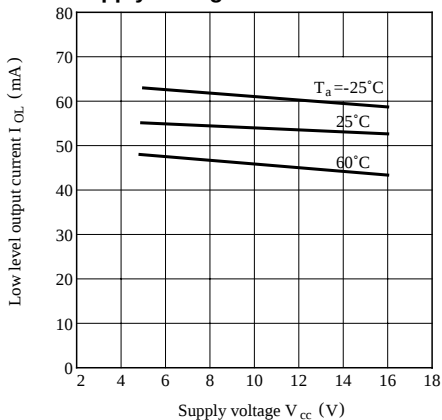


Fig.10 Sensitivity Diagram ($T_a = 25^\circ\text{C}$)

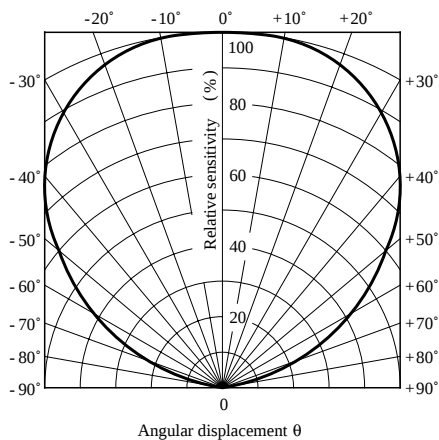
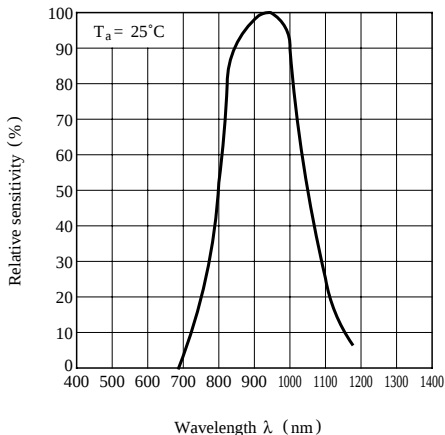
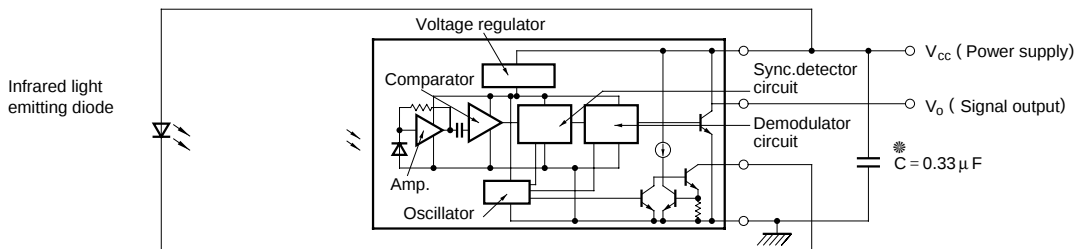


Fig.11 Spectral Sensitivity



Basic Circuit



⌘ In order to stabilize power supply line, connect a by-pass capacitor of 0.33 μF or more between V_{CC} and GND near the device.

● Please refer to the chapter "Precautions for Use."